



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

# 35  
Amdt H  
D. Smalls-Logan  
1-2803

In re the Application of: )  
)  
NISHIMOTO et al ) Art Unit: 2823  
)  
Serial No.: 08/897,839 ) Examiner: K. Eaton  
)  
Filed: July 21, 1997 )  
)  
For: STRESS-ADJUSTED INSULATING )  
FILM FORMING METHOD, )  
SEMICONDUCTOR DEVICE AND )  
METHOD OF MANUFACTURING THE )  
SAME )

RESPONSE TO OFFICE ACTION OF JANUARY 10, 2003

Assistant Commissioner for Patents  
Washington, D.C. 20231

Sir:

Responsive to the office action of January 10, 2003, please amend the captioned application as follows:

IN THE CLAIMS:

Please rewrite claim 43 as follows:

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43. (Amended Three Times) A stress-adjusted insulating film forming method for forming a multilayered insulating film on a substrate, said method comprising:

(a) forming a first insulating layer with compressive stress;